
Seminar

Electronic transport in InAs/GaSb composite quantum well: A candidate for 2D topological insulator

Atindra Nath Pal

Solid State Physics Laboratory, ETH Zurich, Switzerland

In this talk, I will present transport measurements on InAs/GaSb composite quantum well, an emerging candidate for 2d topological insulator. By making Hall bar devices it was possible to observe both electron and hole transport by tuning a top gate voltage. I will discuss the quantum Hall effect near the charge neutrality point, where we observe a strong nonlocal response due to the presence of helical edge channels. Finally I will show the recent measurements where we get the indication of topological edge states at zero magnetic field.

Thursday, Apr 16th 2015

11:30 AM (Tea/Coffee at 11:45 AM)

Seminar Hall, TCIS